

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L18	2	(semiconductor with first adj conductivity and second with conductivity with "source/drain" and contact and electrical adj connection and silicide and "n-type").clm.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:46

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	16	("20030218209" "20050017298" "4455565" "5155563" "5252848" "5841166" "5869875" "5907173" "5912490" "5949104" "6001710" "6215152" "6372557" "6521923" "6831332" "6838731"). PN.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:19
L2	185	("20030218209" "20050017298" "4455565" "5155563" "5252848" "5841166" "5869875" "5907173" "5912490" "5949104" "6001710" "6215152" "6372557" "6521923" "6831332" "6838731")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:09
L3	85	2 and transistor with (substrate with (source drain))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:20
L4	54	3 and transistor with (substrate with (source drain)) same ((n p first second) near3 type)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:21
L5	54	4 and gate	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:11
L6	21	5 and silicide	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:13
L7	9	6 and "LDMOS"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:15
L8	6	("5463241"   "5841166"   "5869875"   "5981983"   "6222233"   "6372557"). PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/20 13:13
L9	4	("4012764"   "5321285"   "5567976"   "5629546").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/20 13:14
L10	9	6 and "LDMOS"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:20
L11	7	("5055896"   "5252848"   "5841166"   "5907173"   "5949104"   "6215152"   "6521923").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/20 13:17
L12	5823	257/343-344,408-409,335-335, 285-288.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:20
L13	9	10 and "LDMOS"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:20

## EAST Search History

L14	85	3 and transistor with (substrate with (source drain))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:20
L15	54	14 and transistor with (substrate with (source drain)) same ((n p first second) near3 type)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:35
L16	1	10/673539	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:43
L17	5	(semiconductor with first adj conductivity and second with conductivity with "source/drain" and contact and electrical adj connection). clm.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:45
L18	2	(semiconductor with first adj conductivity and second with conductivity with "source/drain" and contact and electrical adj connection and silicide and "n-type").clm.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/08/20 13:46